

Abstracts

C-Band 10 Watt MMIC Amplifier Manufactured Using Refractory SAG Process

I.J. Bahl, R. Wang, A. Geissberger, E. Griffin and C. Andricos. "C-Band 10 Watt MMIC Amplifier Manufactured Using Refractory SAG Process." 1989 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 89.1 (1989 [MCS]): 21-24.

The design and performance of a C-Band single chip GaAs MMIC Amplifier manufactured using the refractory self-aligned gate process is described. The amplifier demonstrates 10 watts power output at 5.5 GHz with associated gain of 5 dB and power added efficiency of 36%. The functional yield of the IC on the best wafer was 70%. To our knowledge, these results exceed the best published results for C-Band power MMIC amplifiers.

 [Return to main document.](#)